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Rev 0

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# Freescale Menoigenductor, Inc.

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Supply Voltage	VCC	5.0	V
IF Input	IF In+, IF In–	10	dBm
LO Input	LO	10	dBm
Operating Temperature	ТА	-40 to 85	°C
Storage Temperature	T <sub>stg</sub>	-65 to 150	°C

NOTES: 1. Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the limits in the Recommended Operating

Conditions and Electrical Characteristics tables or Pin Descriptions section.

2. Meets Human Body Model (HBM)  $\leq$ 50 V and Machine Model (MM)  $\leq$ 40 V. This device is rated

Moisture Sensitivity Level (MSL) 4. ESD data available upon request.

### **RECOMMENDED OPERATING CONDITIONS**

Characteristic	Symbol	Min	Тур	Max	Unit
Supply Voltage	VCC	2.7	-	3.6	V
RF Frequency Range	<sup>f</sup> RF	1700	-	2000	MHz
IF Frequency Range	fIF	70	-	250	MHz
LO Frequency Range	fLO	1500	-	2100	MHz
Gain Control Voltage Range	IF V <sub>cntrl</sub> , RF V <sub>cntrl</sub>	0.1	-	1.7	V

# **ELECTRICAL CHARACTERISTICS** ( $V_{CC} = 2.7 \text{ V}$ , $P_{LO} = -13 \text{ dBm} @ 2010 \text{ MHz}$ , $P_{IF} = -27 \text{ dBm}$ (differential) @ 130 MHz, $V_{Enable1} = V_{Enable2} = 2.4 \text{ V}$ , $T_A = -40 \text{ to } 85^{\circ}\text{C}$ , Test Circuit in Figure 1, unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
CASCADE PERFORMANCE (Filter included between RF Out and Excite	r input. Filter inse	rtion loss is 4.	.0 dB)		1
Output Power	Pout				dBm
$V_{\text{Ctrl}} = 1.7 \text{ V}$		3.0	5.0	-	
V <sub>ctrl</sub> = 1.3 V		2.0	3.8	_	
Dynamic Range (V <sub>ctrl</sub> = 0.1 to 1.7 V)	DR	50	65	-	dB
Adjacent Channel Power @ 1.25 MHz Offset	ACPR				dBc
High Current (Bias Select = 0.4 V, $P_{out}$ = 3.0 dBm (set by $V_{ctrl}$ ) )		-52	-58	-	
Supply Current	ICC				mA
High Current (Bias Select = 0.4 V)		-	55	80	
Low Current (Bias Select = 2.4 V)		-	35	50	
MIXER SECTION					
Conversion Gain	GC	-	16	-	dB
Noise Figure	NF	-	12	-	dB
Output Third Order Intercept Point	OIP3	-	6.0	_	dBm
IF AGC Dynamic Range	DRIF	25	38	-	dB
EXCITER SECTION	•				
Gain (No Attenuation)	G	-	24	-	dB
Noise Figure	NF	-	5.0	-	dB
Output Third Order Intercept Point	OIP3	-	22	-	dBm
RF AGC Dynamic Range	DR <sub>RF</sub>	25	38	_	dB



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### **PIN FUNCTION DESCRIPTION**

Pin	Function	Description	Voltage On (V)	Voltage Off (V)
1	IF In+	Mixer IF input pin. Input impedance is 500 $\Omega$ .	–33 dBm (Typ)	
2	Enable 1 (See Table 1)	Enable pin. A logic "High" (>2.4 V) enables entire chip and "Low" (<0.4 V) <b>disables chip.</b>	2.4 to 3.6	0 to 0.4
3	LO In	Mixer LO input pin.	–13 dBm (Typ)	
4	Bias Select	Bias select pin. Logic "Low" (<0.4 V) selects higher current bias for increased linearity and output power. "High" (>2.4 V) selects lower bias for reduced current consumption.		
5	IF AGC Control Voltage	IF AGC gain control pin. A 30 dB dynamic range can be acheived by adjusting voltage from 0.1 V (low gain) to 1.7 V (high gain).	0.1 to 1.7	
6	V <sub>CC3</sub>	Supply Voltage.	2.7 to 3.6	
7	Gnd	Ground connection.	-	
8	VCC1	Supply Voltage	2.7 to 3.6	
9	RF AGC Control Voltage	RF AGC control pin. A 30 dB dynamic range can be acheived by adjusting voltage from 0.1 V (low gain) to 1.7 V (high gain).	0.1 to 1.7	
10	Exciter Out	RF exciter amplifier output pin.	-	
11	Enable 2 (See Table 1)	Tx Enable pin. A logic "High" (>2.4 V) enables Tx path and "Low" (<0.4 V) disables Tx path except LO Buffer.	2.4 to 3.6	0 to 0.4
12	V <sub>CC2</sub>	Supply Voltage	2.7 to 3.6	
13	Exciter In	RF exciter amplifier input pin.	-	
14	Gnd	Ground connection.	-	
15	Gnd	Ground connection.	-	
16	Gnd	Ground connection.	-	
17	RF Out-	Mixer RF output pin.		
18	RF Out+	Mixer RF output pin.		
19	V <sub>CC4</sub>	Supply Voltage	2.7 to 3.6	
20	IF In–	Mixer IF input pin. Input impedance is 500 $\Omega$ .	–33 dBm (Typ)	

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### Table 1. Enable Truth Table

Enable 1	Enable 2	Mode
0	0	Disabled
0	1	Not Applicable
1	0	Standby Mode: Disables mixer/exciter, except LO buffer
1	1	Tx Enabled



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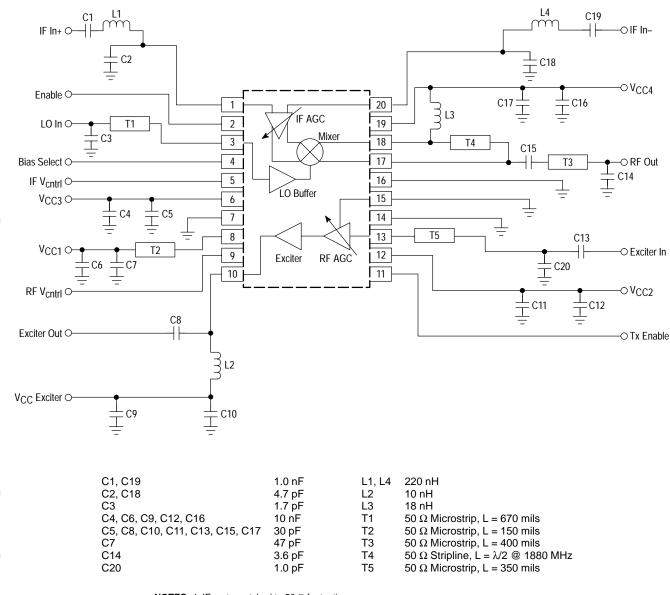
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Figure 1. Application Circuit



**NOTES:** 1. IF ports matched to 50  $\Omega$  for testing purposes.

2. Microstrip line and C7 form part of RF AGC/Exciter interstage match.

3. Er = 4.45 and board thickness = 18 mils.

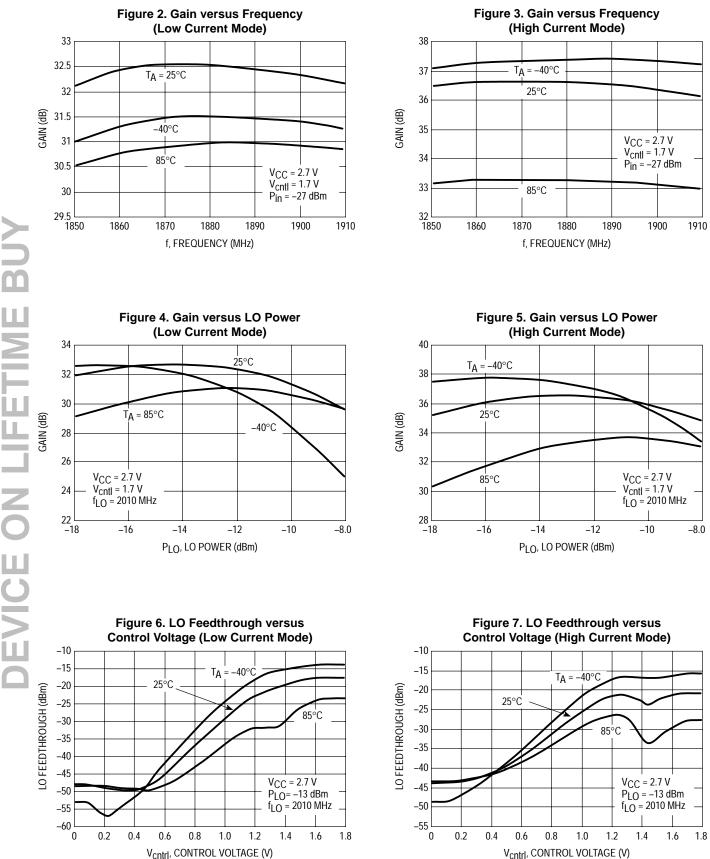


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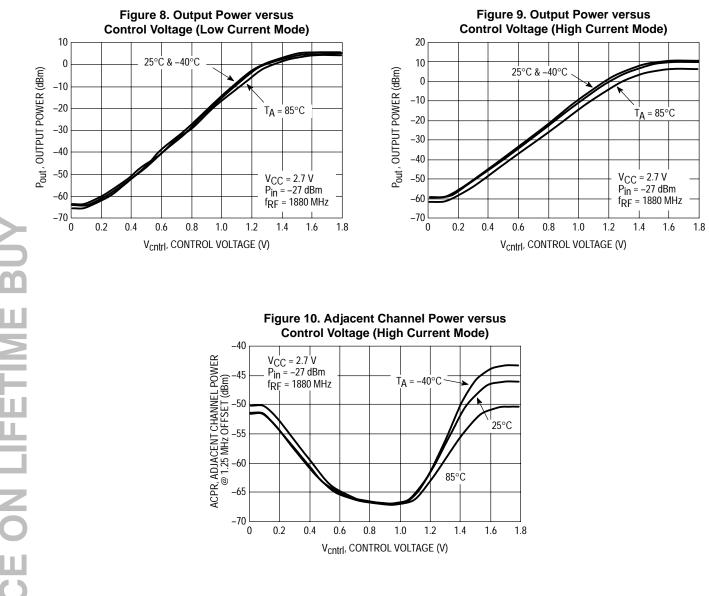




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**APPLICATION INFORMATION** 

#### **Design Philosophy**

The MRFIC1854A has three operating states, enable, standby, and disable. These states are controlled by the truth table shown in Table 1. The device is fully operational during the enable state and the bias level can be selected. A high bias current for maximum power CDMA or a lower bias current for CDMA at lower powers can be selected via the Bias Select pin. In the high current CDMA mode, the quiescent current is increased to maximize the linearity of the device. In the lower current bias state, the guiescent current is reduced to save current during lower power CDMA operation. The standby mode can be used to reduce current consumption during Voice Activity Factoring. In the standby mode, the LO buffer remains on to prevent VCO pulling and the bandgap reference bias circuit remains on to assure rapid device turn on. Current consumption in standby mode is 10 mA typical. The disable mode is used to turn the MRFIC1854A completely off. Leakage current in this mode is only a few microamps.

The mixer is a double-balanced "Gilbert-cell" design with a balanced LO buffer amplifier. The input and output of the mixer are differential. The IF AGC is a differential amplifier that uses the "current steering" method for gain control. The IF AGC/mixer combination has 16 dB of gain and typically draws 20 mA quiescent current in the CDMA mode. An external filter is required between the mixer and RF AGC amplifier to reduce RX band noise.

Figure 1 shows the applications circuit for the MRFIC1854A. In this circuit, the IF ports of the IF AGC have been matched to 50  $\Omega$  for testing purposes. In the actual application, the differential IF ports of the mixer would be impedance matched to an IF SAW filter. The differential impedance of the IF ports is 1600 ohms. The RF output of the mixer is configured as a differential output. A stripline balun is used to convert the RF output to single ended. DC current to the open collector output of the mixer is provided by inductor, L3 (18 nH) and transmission line, T4. Transmission lines T3 and T4, and capacitors C15 (30 pF) and C14 (3.6 pF) form the balun/output match for the mixer.

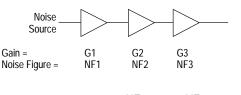
The RF AGC amplifier is a single–ended cascode design employing the standard "current steering" method of gain control. It's ground is brought out through pin number 15 so inductance can be added to degenerate the gain for a lower noise floor. The maximum gain is around 13 dB. It typically draws 9.0 mA quiescent current in CDMA mode. The RF V<sub>cntrl</sub> signal is buffered with an on-chip OpAmp then preconditioned with temperature compensation and dB/V linearization before being applied to the RF AGC amplifier.

Transmission line T2 and capacitor C7 (47 pF) are for the interstage match between the RF AGC and the exciter amplifier.

The exciter amplifier is a simple common emitter design. It is grounded directly to the exposed pad which results in 12 dB of gain. It typically draws 24 mA bias current in CDMA. Inductor L2 (10 nH), capacitor C8 (30 pF), and C10 (30 pF) provide the output matching. L2 also provides a DC current path for the open collector output.

#### **Noise Power Considerations**

In CDMA systems, the handset is required to dynamically adjust its output power to specific levels. This requires a dynamic range of as much as 90 dB from the transmitter. Another key performance specification in CDMA systems is the output noise power, both in band and out of band. Noise power specifications has caused the noise figure of the transmitter to become an important system consideration. The cascaded noise figure of the transmitter can be analyzed with the same equation used in receiver analysis. The only difference is the noise source is from the transmitter (modulator) instead of the atmosphere.



$$NF_{cascaded} = NF_1 + \frac{NF_2 - 1}{G_1} + \frac{NF_3 - 1}{G_1G_2}$$

This equation above shows that the cascaded noise figure is better if the gain is higher and the noise figure is lower for the stages close to the noise source. For this reason, it is advantageous to implement some of the gain control of a CDMA transmitter in the RF section. The MRFIC1854A integrates a RF AGC amplifier after the upmixer to improve the overall noise figure of the transmitter.



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Table 2. Scattering Parameters for Exciter Ampli	fier
$(V_{DD} = 2.7 \text{ V}, \text{ T}_{A} = 25^{\circ}\text{C}, \text{ RF } \text{V}_{cntrl} = 1.8 \text{ V}, 50 \Omega \text{ Sys}$	tem)

f	S	11	S	21 S <sub>12</sub>		2		S <sub>22</sub>	
(MHz)	s <sub>11</sub>	∠¢	S <sub>21</sub>	∠¢	S <sub>12</sub>	$\angle \phi$	S <sub>22</sub>	∠¢	
1700	0.319	-121.64	15.566	84.09	0.00476	-139.21	0.219	-12.29	
1725	0.315	-123.78	16.291	76.55	0.00415	-126.71	0.222	-24.12	
1750	0.310	-126.93	16.975	68.23	0.00406	-143.61	0.223	-35.58	
1775	0.309	-130.34	17.590	56.64	0.00336	-143.09	0.237	-51.49	
1800	0.304	-132.64	17.834	47.84	0.00406	-144.41	0.248	-64.80	
1825	0.294	-137.08	17.944	35.98	0.00268	-141.85	0.271	-82.53	
1850	0.286	-139.92	17.871	26.91	0.00411	-127.38	0.278	-94.74	
1875	0.274	-141.87	17.591	17.93	0.00286	-132.49	0.298	-104.71	
1900	0.261	-143.08	17.141	9.25	0.00351	-136.62	0.308	-114.83	
1925	0.249	-145.61	16.374	-1.69	0.00447	-139.69	0.324	-128.42	
1950	0.242	-146.86	15.738	-9.57	0.00322	-153.09	0.335	-137.57	
1975	0.233	-148.86	15.046	-17.01	0.00411	-139.41	0.346	-146.12	
2000	0.225	-149.74	14.132	-26.57	0.00490	-139.12	0.350	-155.24	



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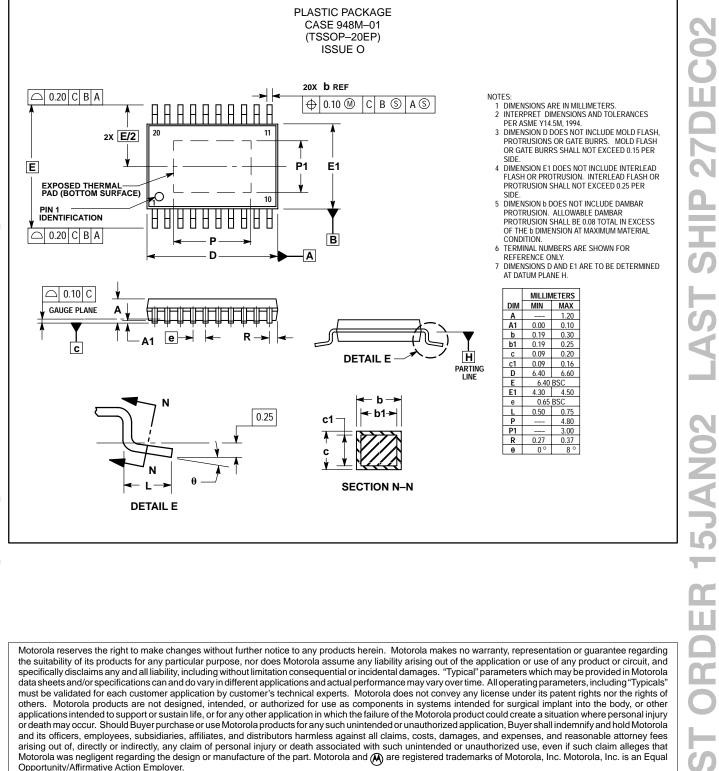
**Table 3. Scattering Parameters for Upmixer**  $(V_{DD} = 2.7 \text{ V}, \text{ T}_{A} = 25^{\circ}\text{C}, \text{ IF } \text{V}_{cntrl} = 1.8 \text{ V}, 50 \Omega \text{ System})$ 

Γ	f		IF In+			IFI		trl = 1.8 V, 5		f	RF Oı	ıt (Pin 17)
	(MHz)	S <sub>11</sub>		)	S <sub>1</sub>	1	∠¢			(MHz)	S <sub>11</sub>	∠ ¢
Ī	70	0.830	) –2.(	)7	0.8	32		-2.24		1700	0.815	-55.16
Ī	80	0.828	3 -2.7	'3	0.8	30		-2.71		1725	0.814	-55.65
Ī	90	0.826	6 –3.0	)1	0.8	28		-2.95		1750	0.814	-56.29
Ī	100	0.826	3 –3.2	21	0.8	27		-3.22		1775	0.817	-56.98
Ī	110	0.822	2 -3.5	57	0.8	25		-3.67		1800	0.820	-57.45
	120	0.821	I –3.7	'4	0.8	23		-3.93		1825	0.823	-58.68
	130	0.821	I –3.9	)3	0.8	23		-4.08		1850	0.825	-59.57
	140	0.818	3 –4.2	25	0.8	20		-4.42		1875	0.826	-60.85
	150	0.818	3 –4.5	54	0.8	21		-4.57		1900	0.825	-62.07
	160	0.818	3 –4.6	61	0.820		-4.76			1925	0.815	-63.81
$\mathbf{m}$	170	0.817	7 –4.8	85				-5.06		1950	0.807	-64.79
	180	0.815	5 –5.′	2	0.8	19	-5.29			1975	0.794	-65.64
	190	0.815	5 –5.2	26	0.819			-5.50	2000		0.782	-66.58
$\geq$	200	0.813	3 -5.4	5	0.816			-5.76				
	210	0.815	5 –5.7	'1	0.8	18		-6.15				
	220	0.812	2 -5.8	32	0.8	16		-6.13				
ш	230	0.811	-6.3	88	0.8	17	-6.54					
	240	0.812	2 -6.5	54	0.8	14	-6.72					
=1	250	0.810	) -6.7	'6	0.8	15	-6.98					
	f	L	O In		f		L	.O In		f		LO In
Z	(MHz)	s <sub>11</sub>	$\angle \phi$		(MHz)	S <sub>11</sub>	1	$\angle \phi$		(MHz)	s <sub>11</sub>	$\angle \phi$
	1500	0.708	-47.83		1725	0.67	7	-54.36		1950	0.624	-58.20
	1525	0.704	-48.38		1750	0.67	0	-55.34		1975	0.623	-59.40
	1550	0.702	-49.02		1775	0.65	54	-56.33		2000	0.612	-60.59
	1575	0.696	-49.55		1800	0.64	1	-56.34		2025	0.605	-61.04
U	1600	0.694	-50.11		1825	0.63	86	-56.65		2050	0.599	-61.70
VIC	1625	0.691	-50.83		1850	0.63	31	-56.59		2075	0.592	-62.19
	1650	0.688	-51.47		1875	0.63	80	-57.04		2100	0.588	-62.99
Ш	1675	0.691	-52.18		1900	0.62	26	-57.38				
	1700	0.681	-53.42		1925	0.62	22	-57.84				



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